

FGW60N65WE

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Discrete IGBT

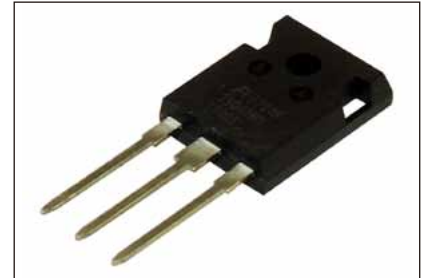
Discrete IGBT (High-Speed W series) 650V / 60A

Features

- Low power loss
- Low switching surge and noise
- High reliability, high ruggedness (RBSOA, SCSOA etc.)

Applications

- Uninterruptible power supply
- PV Power conditioner
- Inverter welding machine



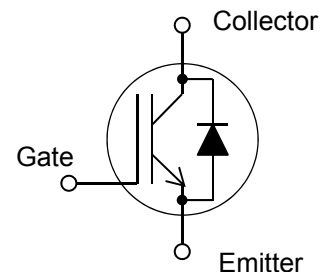
Maximum Ratings and Characteristics

Absolute Maximum Ratings at $T_J=25^\circ\text{C}$ (unless otherwise specified)

Items	Symbols	Characteristics	Unit	Remarks
Collector-Emitter Voltage	V_{CES}	650	V	
Gate-Emitter Voltage	V_{GES}	± 20	V	
Transient Gate-Emitter Voltage		± 30	V	$T_r < 1\mu\text{s}$
DC Collector Current	$I_{C@25}$	83	A	$T_c=25^\circ\text{C}$
	$I_{C@100}$	60	A	$T_c=100^\circ\text{C}$
Pulsed Collector Current	I_{CP}	240	A	Note *1
Turn-Off Safe Operating Area	-	240	A	$V_{CE} \leq 650\text{V}$ $T_J \leq 175^\circ\text{C}$
Diode Forward Current	$I_F@25$	88	A	
	$I_F@100$	60	A	
Diode Pulsed Current	I_{FP}	240	A	Note *1
IGBT Max. Power Dissipation	P_{D_IGBT}	405	W	$T_c=25^\circ\text{C}$
FWD Max. Power Dissipation	P_{D_FWD}	220	W	$T_c=25^\circ\text{C}$
Operating Junction Temperature	T_J	$-40 \sim +175$	$^\circ\text{C}$	
Storage Temperature	T_{stg}	$-55 \sim +175$	$^\circ\text{C}$	

Note *1 : Pulse width limited by T_{Jmax} .

Equivalent circuit



Electrical characteristics at $T_J = 25^\circ\text{C}$ (unless otherwise specified) Static Characteristics

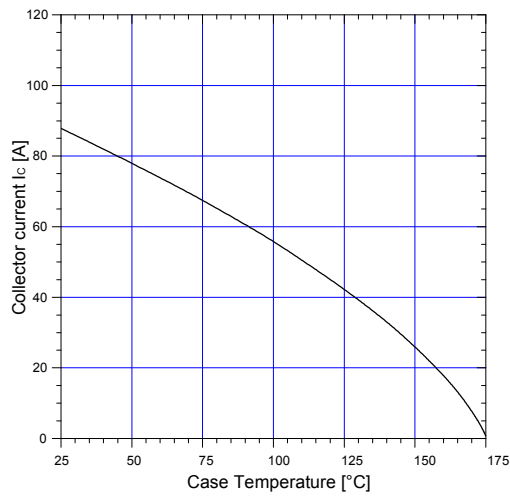
Description	Symbol	Conditions	min.	typ.	max.	Unit
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 650\text{V}, V_{GE} = 0\text{V}$ $T_J=25^\circ\text{C}$ $T_J=175^\circ\text{C}$	-	-	250 2	μA mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{V}, V_{GE} = \pm 20\text{V}$	-	-	200	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}, I_C = 60\text{mA}$	3.0	4.0	5.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{V}, I_C = 60\text{A}$ $T_J=25^\circ\text{C}$ $T_J=125^\circ\text{C}$ $T_J=175^\circ\text{C}$	-	1.80 2.05 2.10	2.20	V
Input Capacitance	C_{ies}	$V_{CE}=25\text{V}$	-	4300	-	pF
Output Capacitance	C_{oes}	$V_{GE}=0\text{V}$	-	125	-	
Reverse Transfer Capacitance	C_{res}	$f=1\text{MHz}$	-	95	-	
Gate Charge	Q_G	$V_{CC} = 520\text{V}$ $I_C = 60\text{A}$ $V_{GE} = 15\text{V}$	-	250	-	nC
Turn-On Delay Time	$t_{d(on)}$	$T_J = 25^\circ\text{C}, V_{CC} = 400\text{V}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $R_G = 10\Omega, L = 500\mu\text{H}$ Energy loss include "tail" and FWD reverse recovery.	-	29	-	ns
Rise Time	t_r		-	45	-	
Turn-Off Delay Time	$t_{d(off)}$		-	260	-	
Fall Time	t_f		-	78	-	
Turn-On Energy	E_{on}	$T_J = 150^\circ\text{C}, V_{CC} = 400\text{V}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $R_G = 10\Omega, L = 500\mu\text{H}$ Energy loss include "tail" and FWD reverse recovery.	-	0.60	-	mJ
Turn-Off Energy	E_{off}		-	0.67	-	
Turn-On Delay Time	$t_{d(on)}$		-	29	-	
Rise Time	t_r		-	45	-	
Turn-Off Delay Time	$t_{d(off)}$	$T_J = 150^\circ\text{C}, V_{CC} = 400\text{V}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $R_G = 10\Omega, L = 500\mu\text{H}$ Energy loss include "tail" and FWD reverse recovery.	-	295	-	ns
Fall Time	t_f		-	68	-	
Turn-On Energy	E_{on}		-	1.05	-	
Turn-Off Energy	E_{off}		-	0.73	-	
Forward Voltage Drop	V_F	$I_F=60\text{A}$ $T_J=25^\circ\text{C}$ $T_J=125^\circ\text{C}$ $T_J=175^\circ\text{C}$	-	2.5 1.9 1.7	3.2	V V V
Diode Reverse Recovery Time	t_{rr}	$V_{CC}=400\text{V}, I_F=30\text{A}$	-	120	-	ns
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt=500\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$	-	0.33	-	μC
Diode Reverse Recovery Time	t_{rr}	$V_{CC}=400\text{V}, I_F=30\text{A}$	-	170	-	ns
Diode Reverse Recovery Charge	Q_{rr}	$-di_F/dt=500\text{A}/\mu\text{s}, T_J=150^\circ\text{C}$	-	1.30	-	μC

● Thermal Resistance

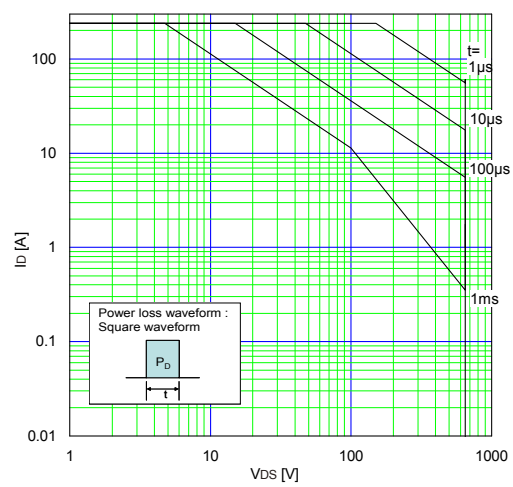
Description	Symbol	min.	typ.	max.	Unit
Thermal Resistance, Junction-Ambient	$R_{th(j-a)}$	-	-	50	°C/W
Thermal Resistance, IGBT Junction to Case	$R_{th(j-c)}_{IGBT}$	-	-	0.366	°C/W
Thermal Resistance, FWD Junction to Case	$R_{th(j-c)}_{FWD}$	-	-	0.676	°C/W

Characteristics (Representative)

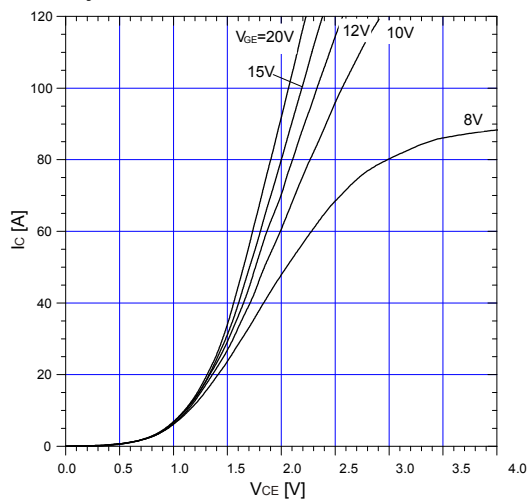
Graph.1
DC Collector Current vs T_c
 $V_{GE} \geq +15V$, $T_j \leq 175^\circ C$



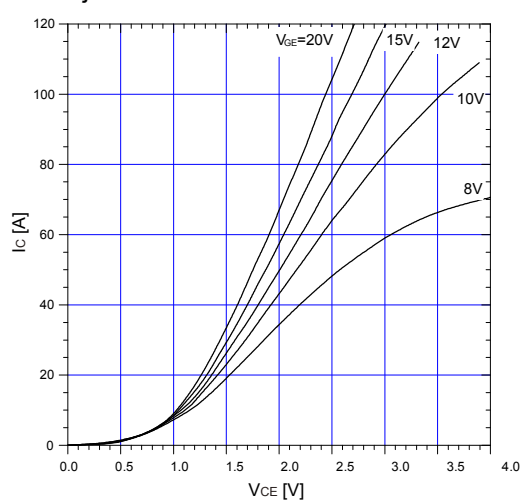
Graph.2
FBSOA
Duty=0(Single pulse), $T_c=25^\circ C$



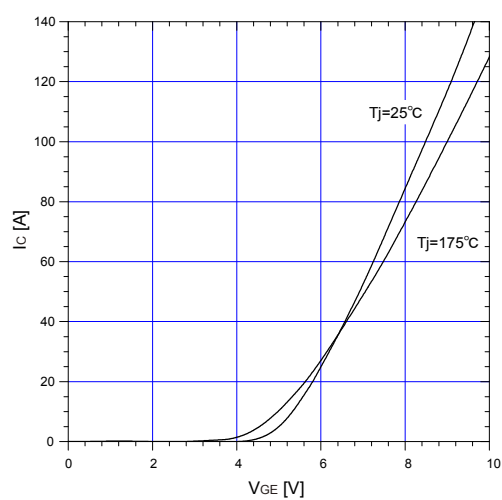
Graph.3
Typical Output Characteristics ($V_{CE}-I_C$)
 $T_j=25^\circ C$



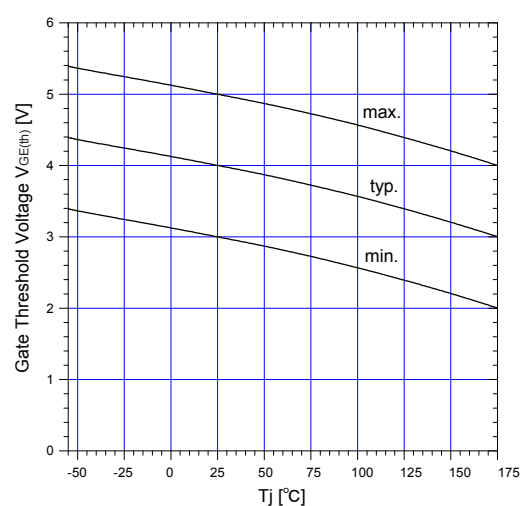
Graph.4
Typical Output Characteristics ($V_{CE}-I_C$)
 $T_j=175^\circ C$



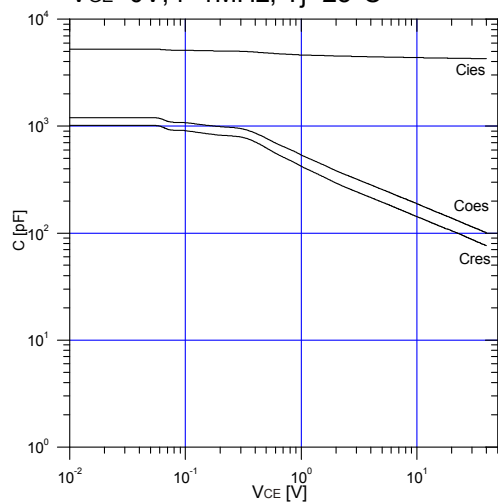
Graph.5
Typical Transfer Characteristics
 $V_{CE}=10V$



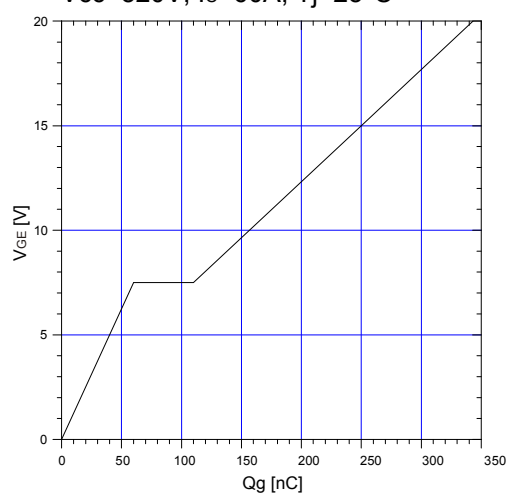
Graph.6
Gate Threshold Voltage vs. T_j
 $I_C=60mA$, $V_{CE}=20V$



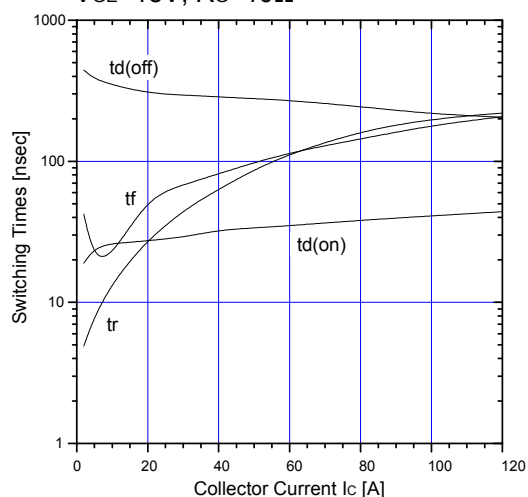
Graph.7
Typical Capacitance
 $V_{GE}=0V$, $f=1MHz$, $T_j=25^\circ C$



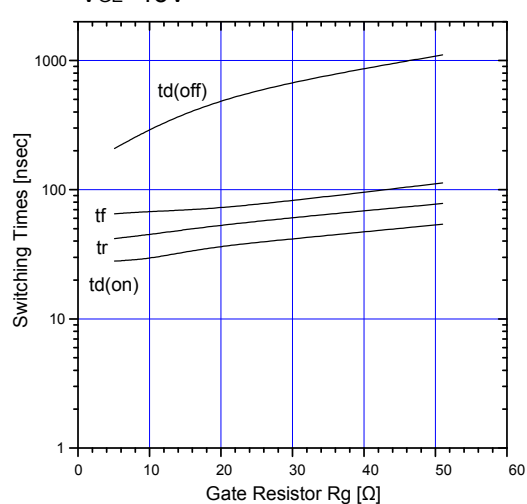
Graph.8
Typical Gate Charge
 $V_{cc}=520V$, $I_c=60A$, $T_j=25^\circ C$



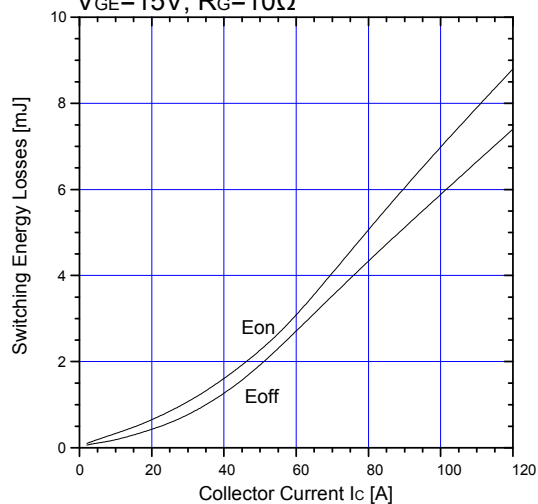
Graph.9
Typical switching time vs. I_c
 $T_j=150^\circ C$, $V_{cc}=400V$, $L=500\mu H$
 $V_{GE}=15V$, $R_G=10\Omega$



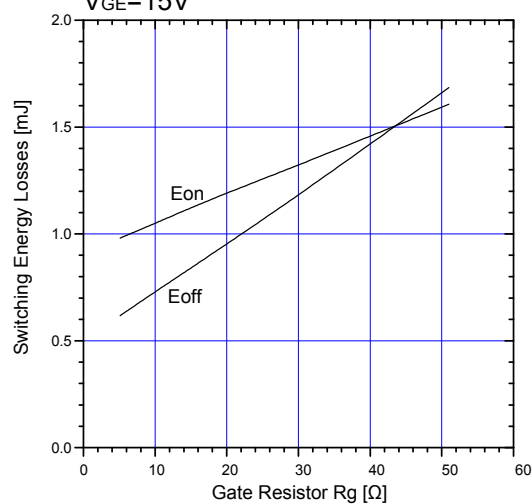
Graph.10
Typical switching time vs. R_g
 $T_j=150^\circ C$, $V_{cc}=400V$, $I_c=30A$, $L=500\mu H$
 $V_{GE}=15V$



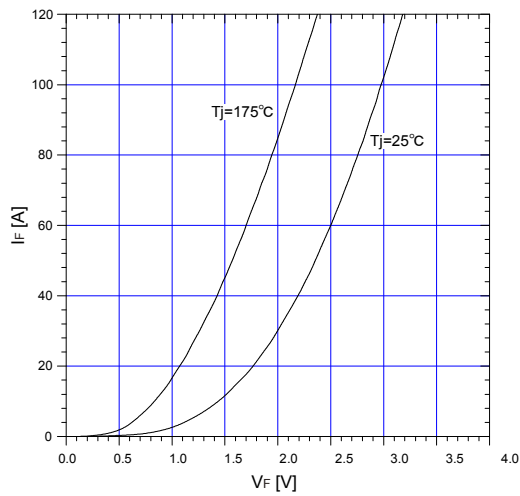
Graph.11
Typical switching losses vs. I_c
 $T_j=150^\circ C$, $V_{cc}=400V$, $L=500\mu H$
 $V_{GE}=15V$, $R_G=10\Omega$



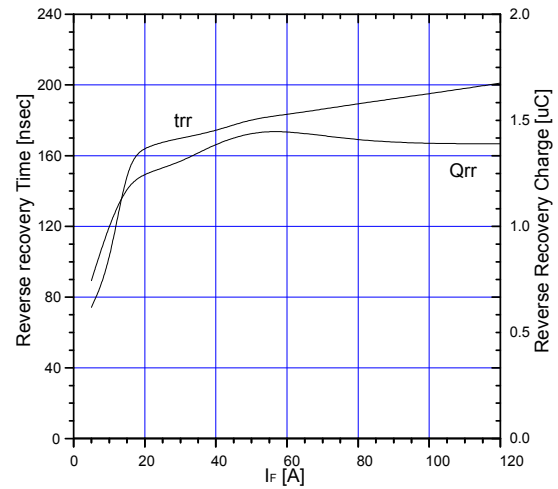
Graph.12
Typical switching losses vs. R_g
 $T_j=150^\circ C$, $V_{cc}=400V$, $I_c=30A$, $L=500\mu H$
 $V_{GE}=15V$



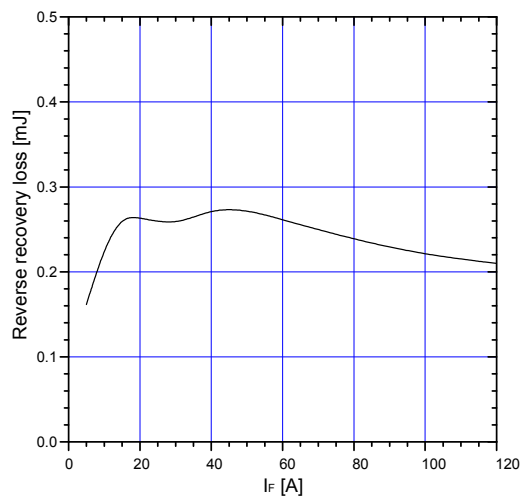
Graph.13
FWD Forward voltage drop (V_F - I_F)



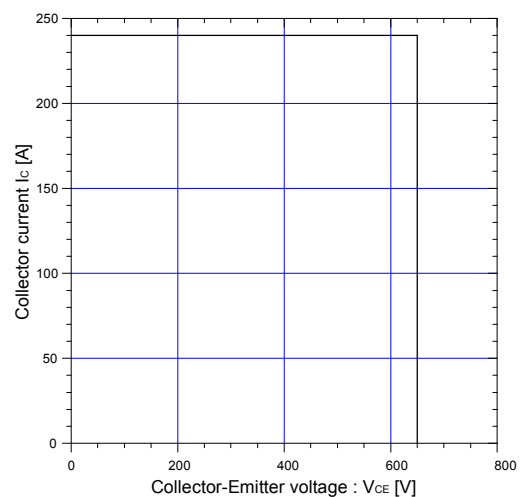
Graph.14
Typical reverse recovery characteristics vs. I_F
 $T_j = 15^\circ\text{C}$, $V_{CC} = 400\text{V}$, $L = 500\mu\text{H}$
 $V_{GE} = 15\text{V}$, $R_G = 10\Omega$

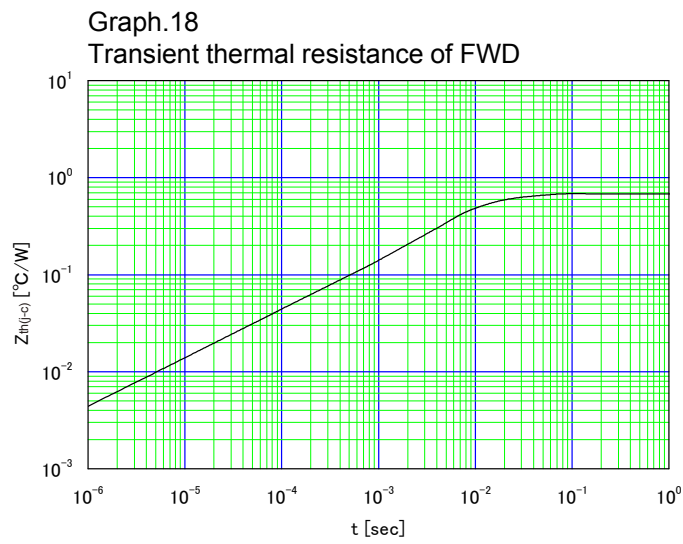
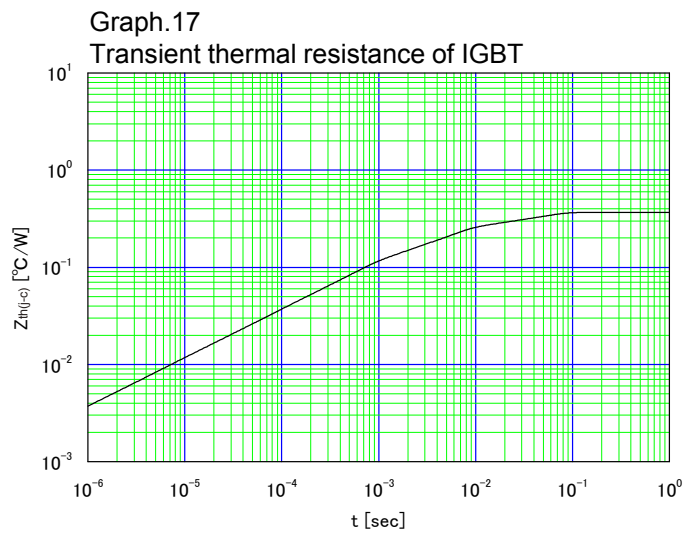


Graph.15
Typical reverse recovery loss vs. I_F
 $T_j = 150^\circ\text{C}$, $V_{CC} = 400\text{V}$, $L = 500\mu\text{H}$
 $V_{GE} = 15\text{V}$, $R_G = 10\Omega$

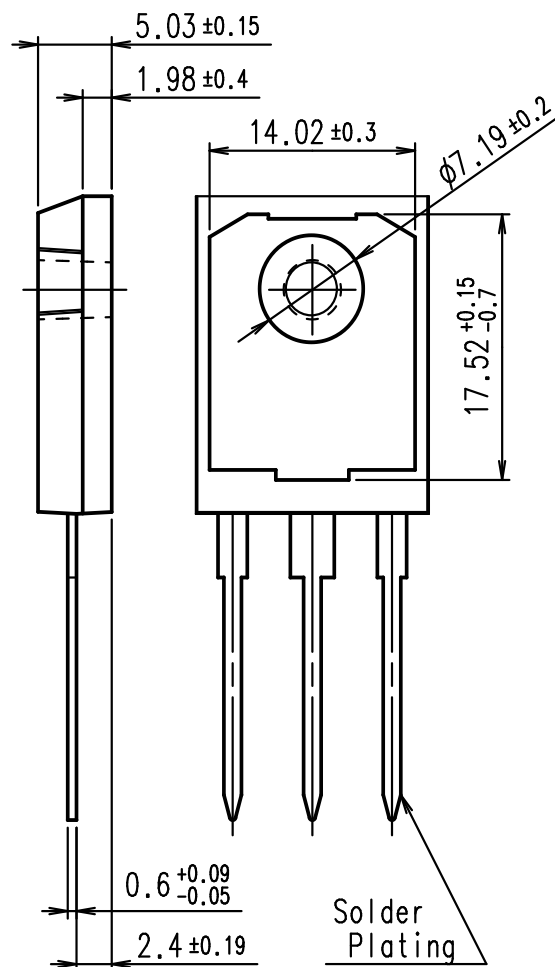
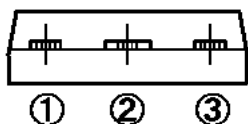
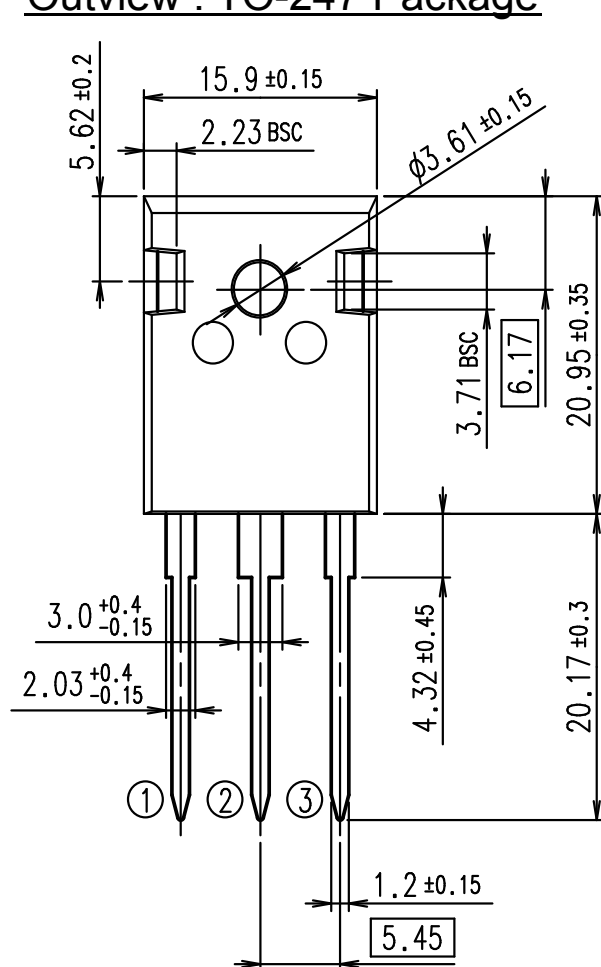


Graph.16
Reverse biased Safe Operating Area
 $T_j \leq 175^\circ\text{C}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 10\Omega$





■ Outline Drawings, mm

Outview : TO-247 Package

CONNECTION

- ① GATE
- ② COLLECTOR
- ③ EMITTER

DIMENSIONS ARE IN MILLIMETERS.

WARNING

1. This Catalog contains the product specifications, characteristics, data, materials, and structures as of September 2016. The contents are subject to change without notice for specification changes or other reasons. When using a product listed in this Catalog, be sure to obtain the latest specifications.
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• Machine tools	• Audiovisual equipment	• Electrical home appliances	• Personal equipment
			• Industrial robots etc.
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• Submarine repeater equipment		
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IGBT Modules

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